A1 When an electric signal is applied to the gate electrode of the TFT "S", a data signal can be applied to the pixel electrode 14. Thus, unless the electric signal is applied to the gate electrode, a data signal cannot be applied to the pixel electrode 14.

Page 7, paragraph beginning on line 9:

A2 For the above-mentioned conventional process for forming the BCB gate-insulating layer, the substrate having a BCB film is in an atmospheric condition during a transfer from the heat oven to the vacuum equipment, after curing. In that case, atmospheric oxygen gas may combine with the surface of the BCB film, or contaminants in the atmosphere may be attached to the surface thereof such that the BCB film is contaminated. If the BCB film has a contaminated surface, an interface property between the BCB gate-insulating layer and the active layer is deteriorated. Returning to FIG. 3, an interface "F" between the gate-insulating layer 33 and active layer 34 directly affects an on-current property of the TFT "S". As mentioned above, if the interface "F" is poor, the electric characteristics of the TFT "S" deteriorates. Returning to FIG. 4 illustrating the conventional process, the BCB film is present in the atmosphere during a transfer between the curing of the BCB film and the forming of the active layer. Then, the surface of the BCB film is contaminated such that the BCB gate-insulating layer made of the BCB film and the active layer which will be formed later have a poor interface property therebetween.